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CHE323/CHE384  
Chemical Processes for Micro- and Nanofabrication

# Lecture 7


## The Junction Diode

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# Junction Diode




- Biasing the p-n junction (applying a voltage between the p-side and the n-side) changes the depletion region width
- In one direction of bias, the depletion region gets bigger, and no current flows
- In the other direction, the depletion region gets smaller and current easily flows
- A device that allows current to flow in only one direction is called a diode

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# Biased P-N Junction

- If we "bias" the diode, apply a voltage V from the p-side to the n-side, almost all of that voltage will fall across the depletion region
- Applied voltage will add or subtract from the built-in voltage to create a junction voltage  $V_0 - V$

$$W = \sqrt{\frac{2\epsilon_{si}(V_0 - V)}{q} \left( \frac{1}{N_A} + \frac{1}{N_D} \right)}$$


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# Biased P-N Junction

- Reverse bias: a negative voltage makes the depletion width larger, and very little current flows (diffusion current is turned back by the higher electric field across the depletion region)

$$W = \sqrt{\frac{2\epsilon_{si}(V_0 - V)}{q} \left( \frac{1}{N_A} + \frac{1}{N_D} \right)}$$

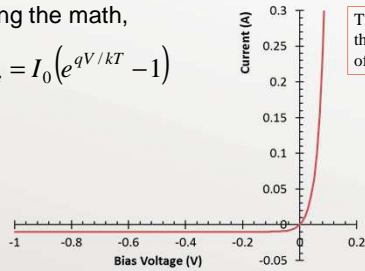
- Forward bias: a positive voltage makes the depletion width smaller, and current can flow (increased diffusion current due to lower electric field/potential barrier)

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# Diode Equation

- Working the math,

$$I_{diode} = I_0 \left( e^{qV/kT} - 1 \right)$$


This is called the I-V curve of the device


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# P-N Junction Capacitance

- Separation of charge produces capacitance
- The capacitance of the p-n junction is easily calculated

For two parallel conducting plates of area A separated by distance W,

$$C = \frac{\epsilon A}{W}$$


$$C_{p-n \text{ junction}} = A \sqrt{\frac{q\epsilon_{si}}{2(V_0 - V)} \left( \frac{N_D N_A}{N_D + N_A} \right)}$$

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## P-N Junction Capacitance

- Example:  $N_A \gg N_D$  (called a p<sup>+</sup>-n junction)

$$C(V) = A \sqrt{\frac{q\epsilon_{Si}}{2(V_0 - V)}} N_D$$

- Measuring  $C(V)$  allows  $N_D$  to be extracted – a common measurement in semiconductor manufacturing

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## Lecture 7: What have we learned?

- How does bias affect depletion width?
- What is a diode?
- Why does a p-n junction act like a diode
- Be able to use the diode equation
- Be able to use the  $C(V)$  equation

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